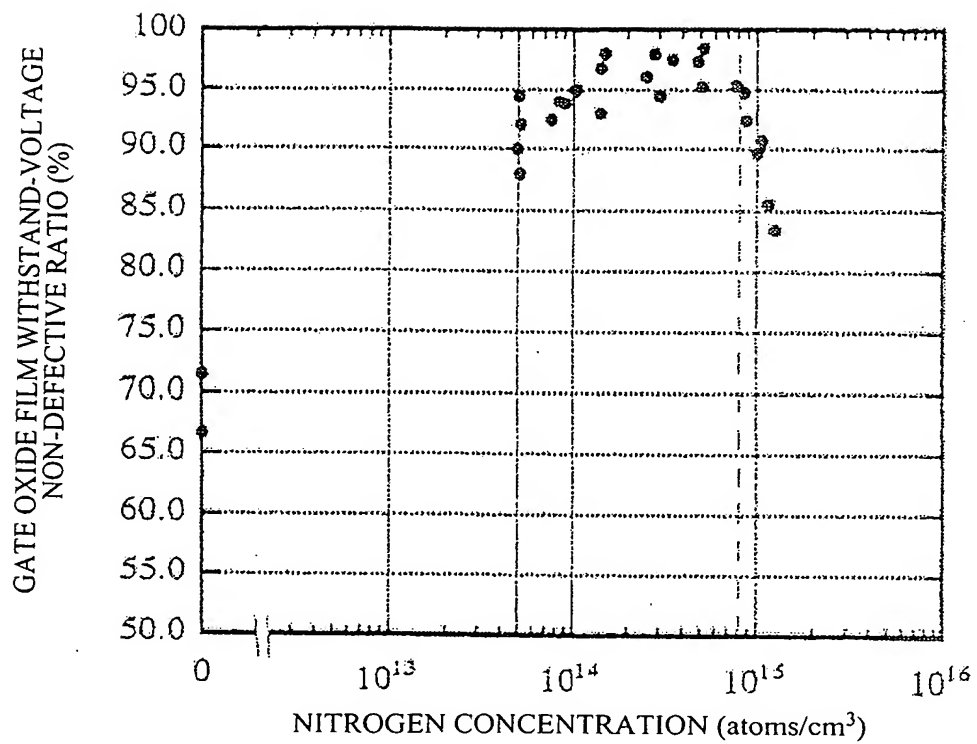


RELATIONSHIP BETWEEN ADDED NITROGEN CONCENTRATION
AND OXIDE FILM WITHSTAND-VOLTAGE NON-DEFECTIVE RATIO
AFTER HYDROGEN ANNEALING

FIG.1



RELATIONSHIP BETWEEN ADDED NITROGEN CONCENTRATION
AND OXIDE FILM WITHSTAND-VOLTAGE NON-DEFECTIVE RATIO
AFTER REMOVAL BY POLISHING SURFACE LAYER OF 3 μm AFTER
HYDROGEN ANNEALING

FIG.2

HYDROGEN ANNEALING (NON-DOPED)

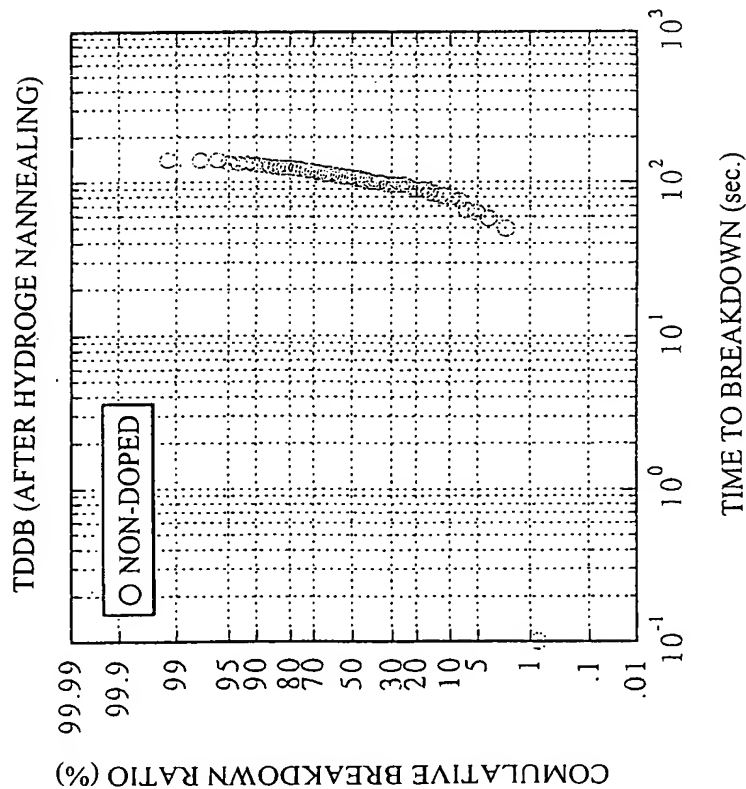


FIG.3(A)

HYDROGEN ANNEALING (N = 5.82E14)

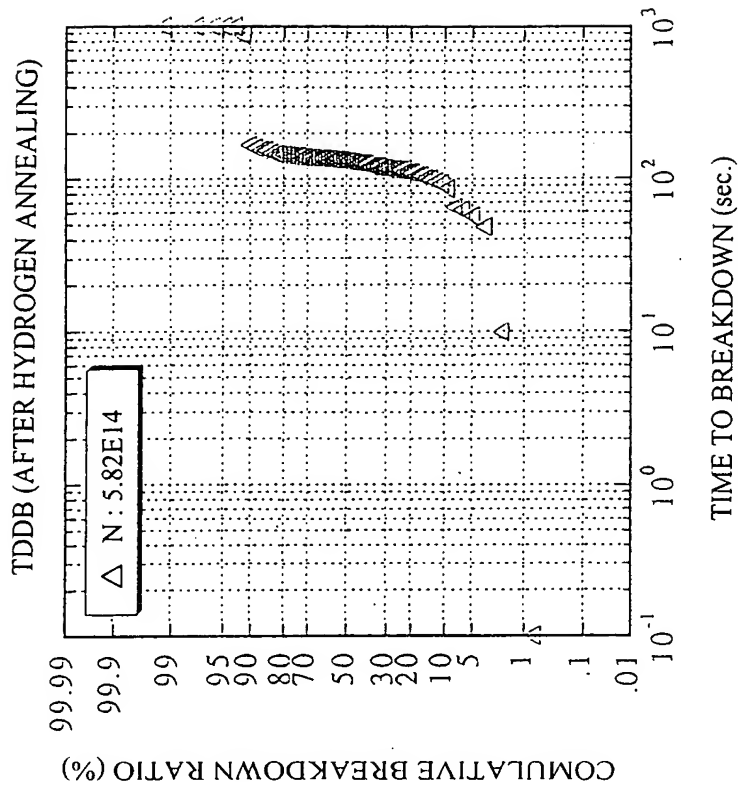


FIG.3(B)

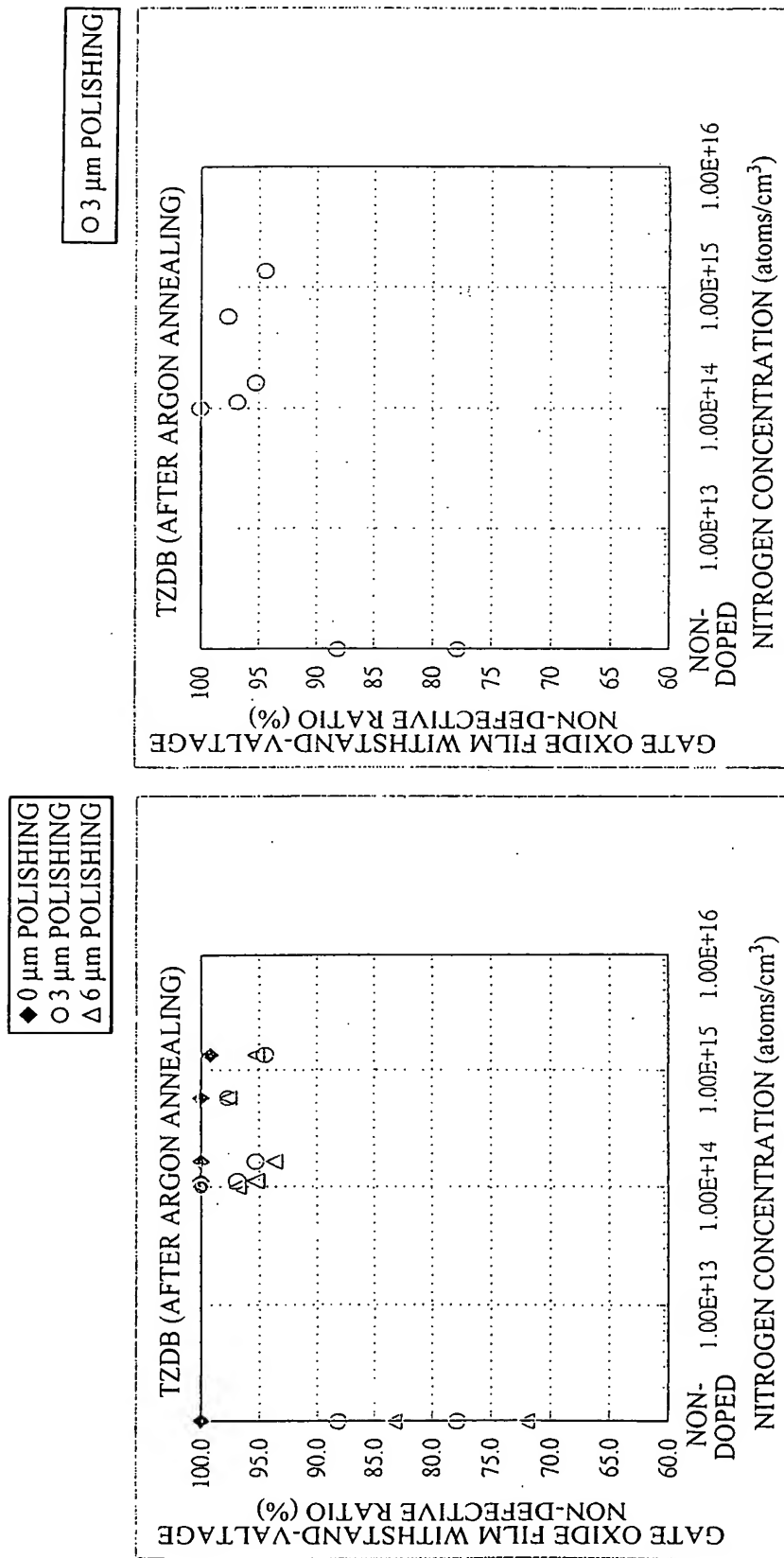
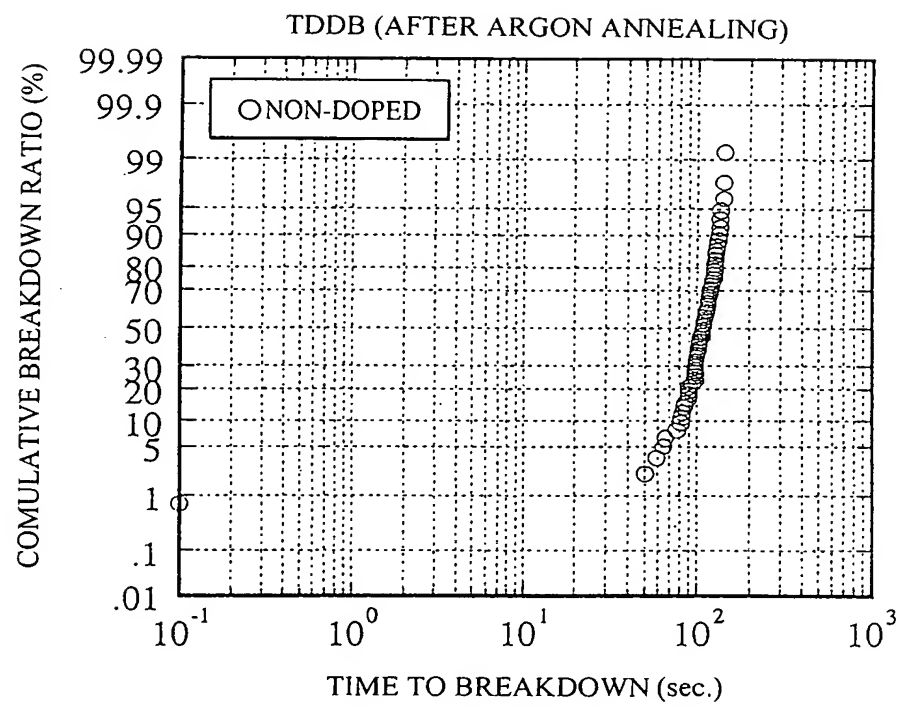
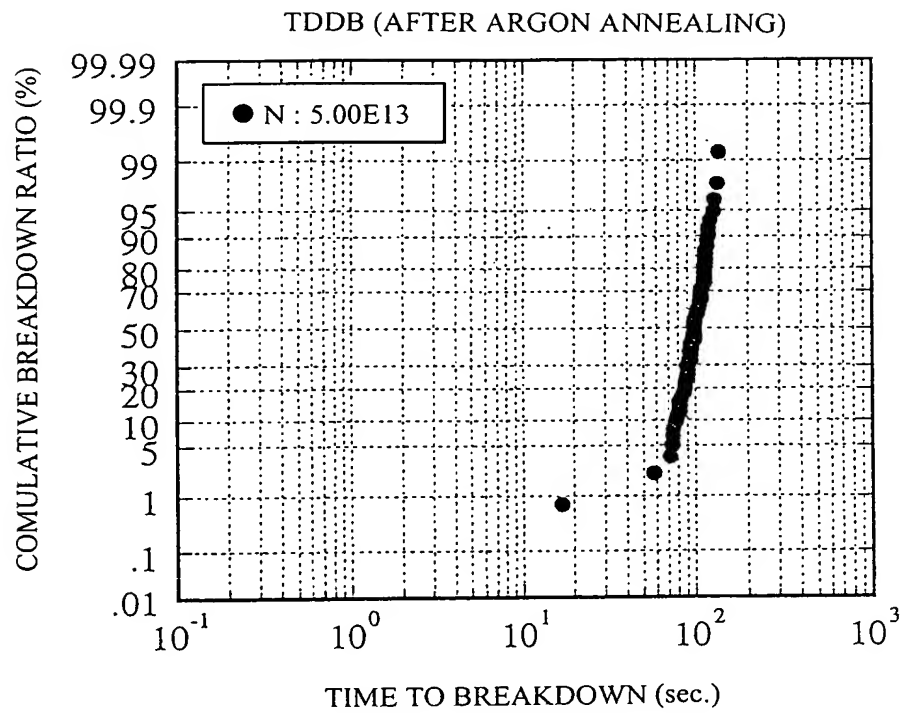
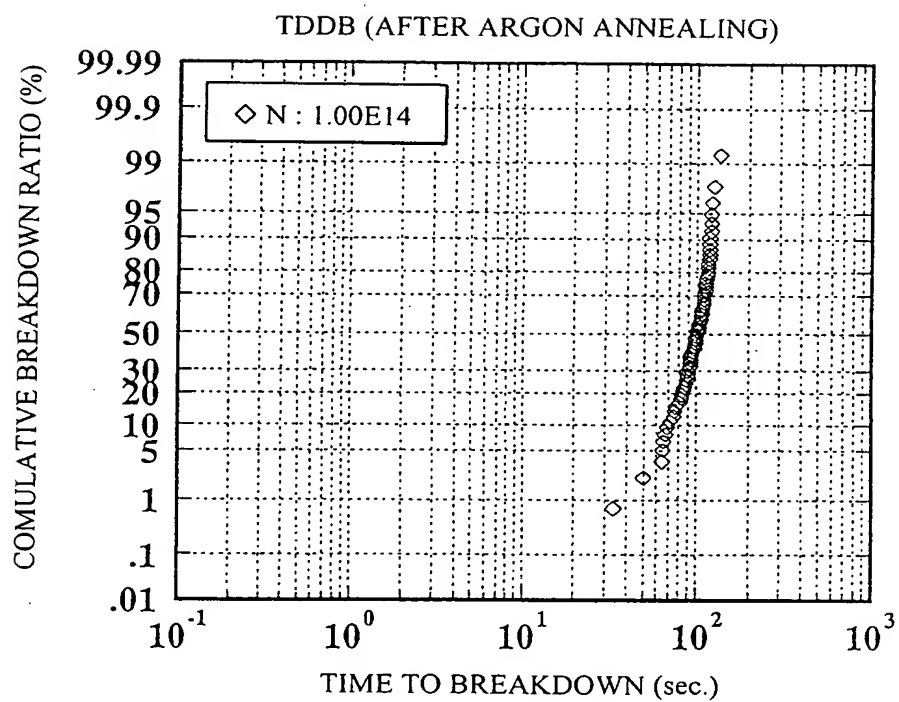


FIG. 4(B)

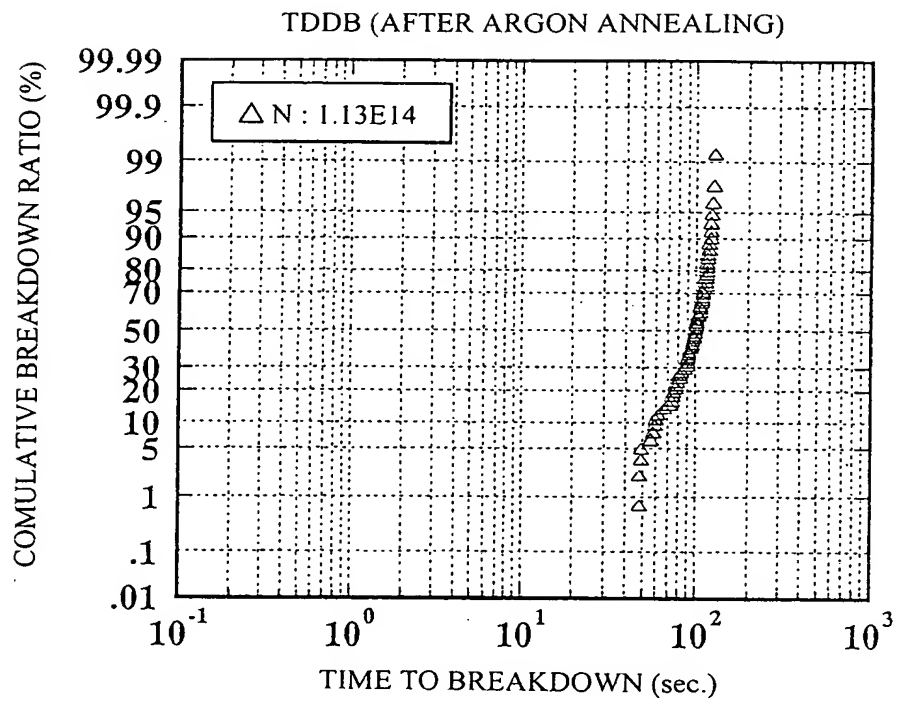
FIG. 4(A)

**FIG.5(A)**

**FIG.5(B)**

**FIG.5(C)**

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**FIG.5(D)**

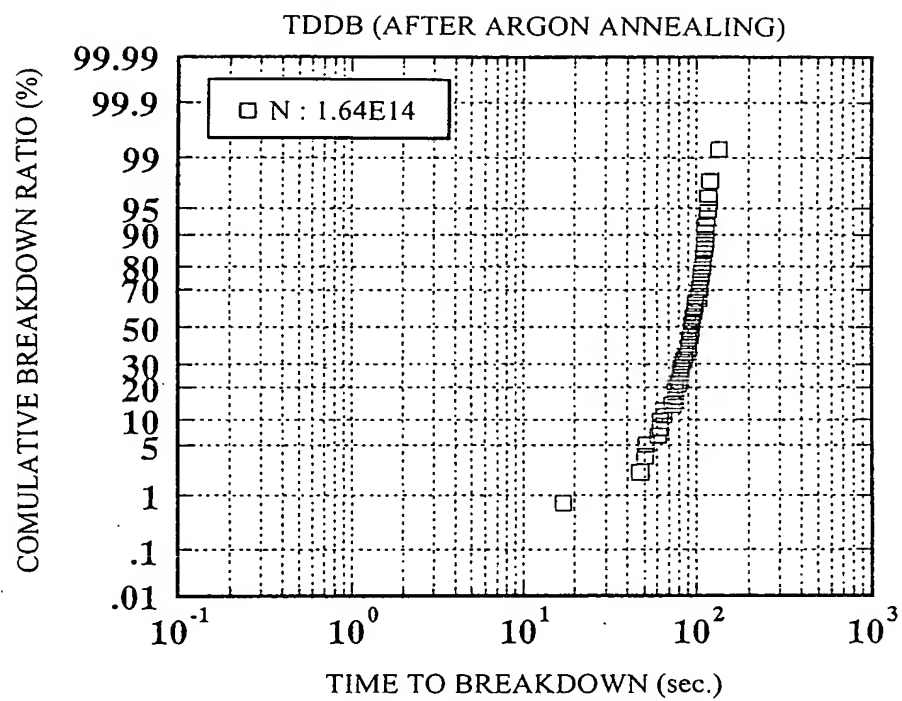
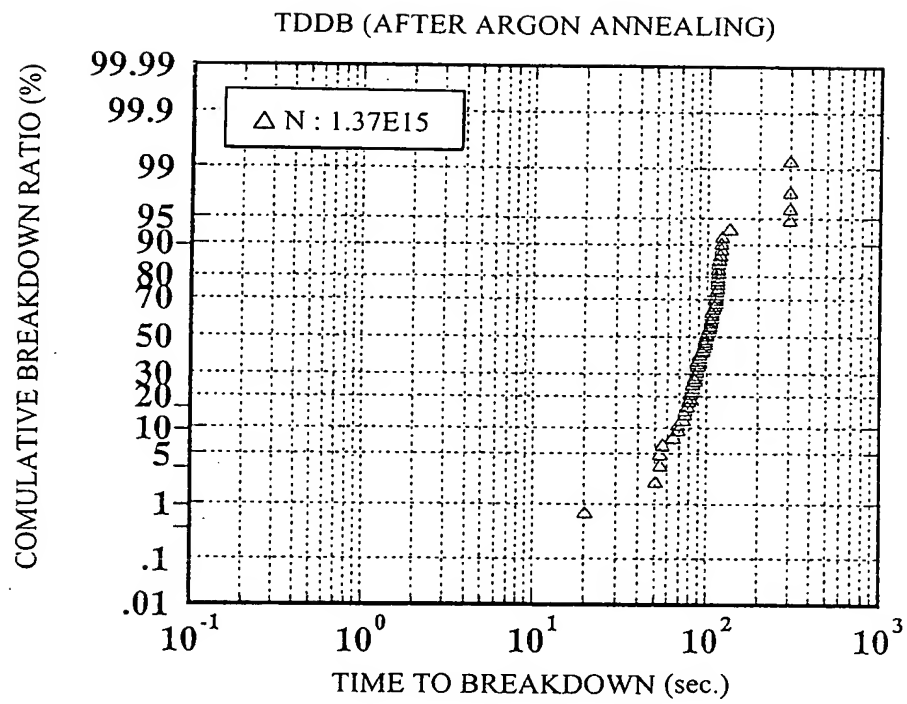


FIG.6(A)



**FIG. 6(C)**

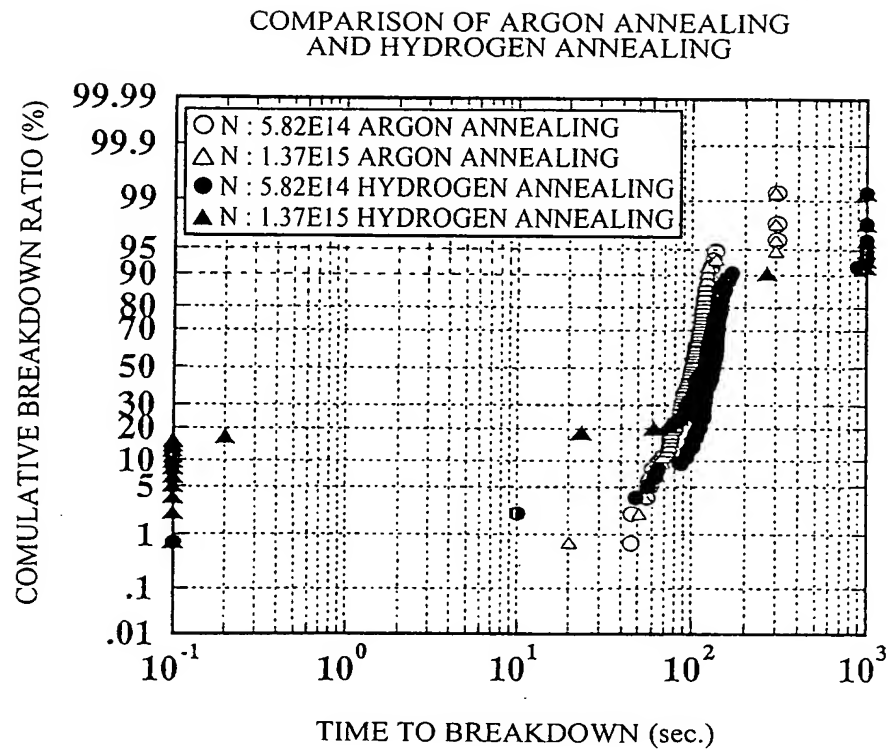


FIG.6(D)

ANNEALING CONDITIONS : 1200C, 1.0hr IN 100% Ar

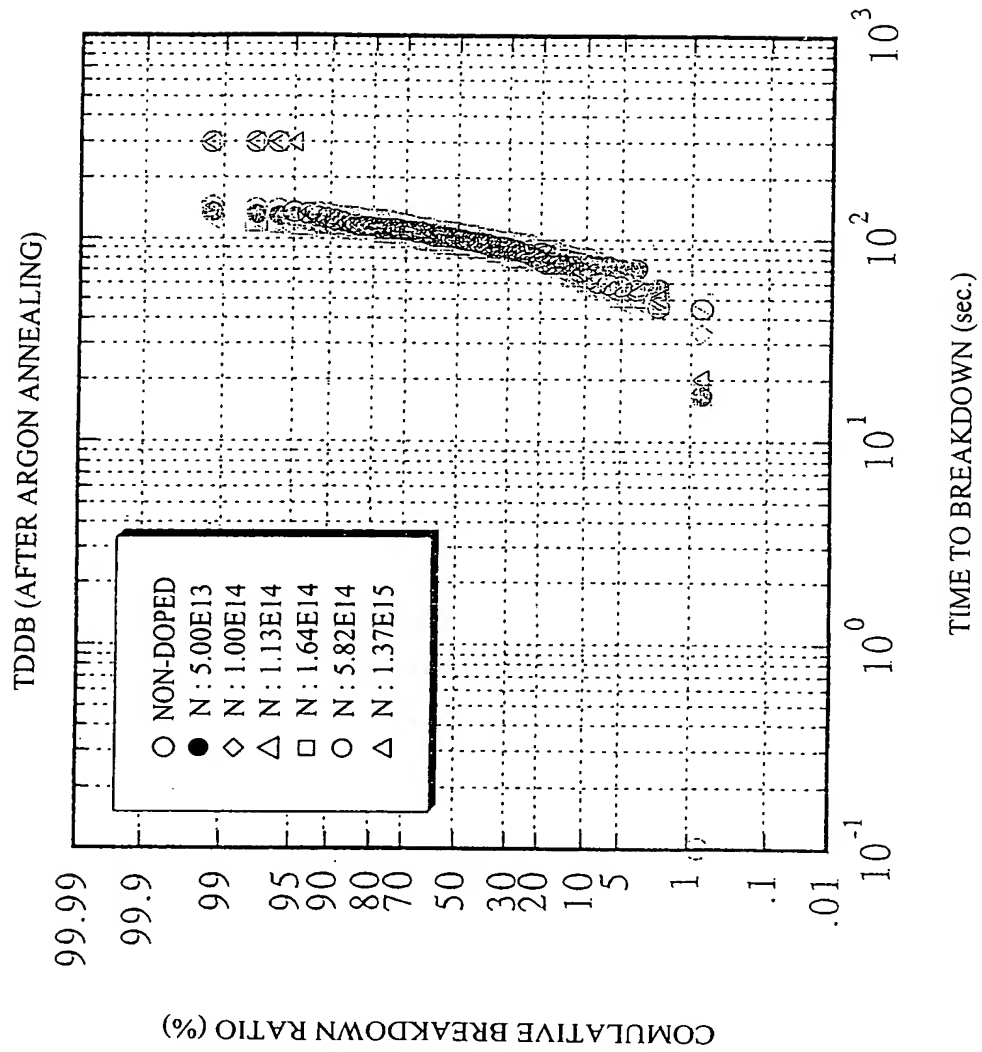


FIG.7

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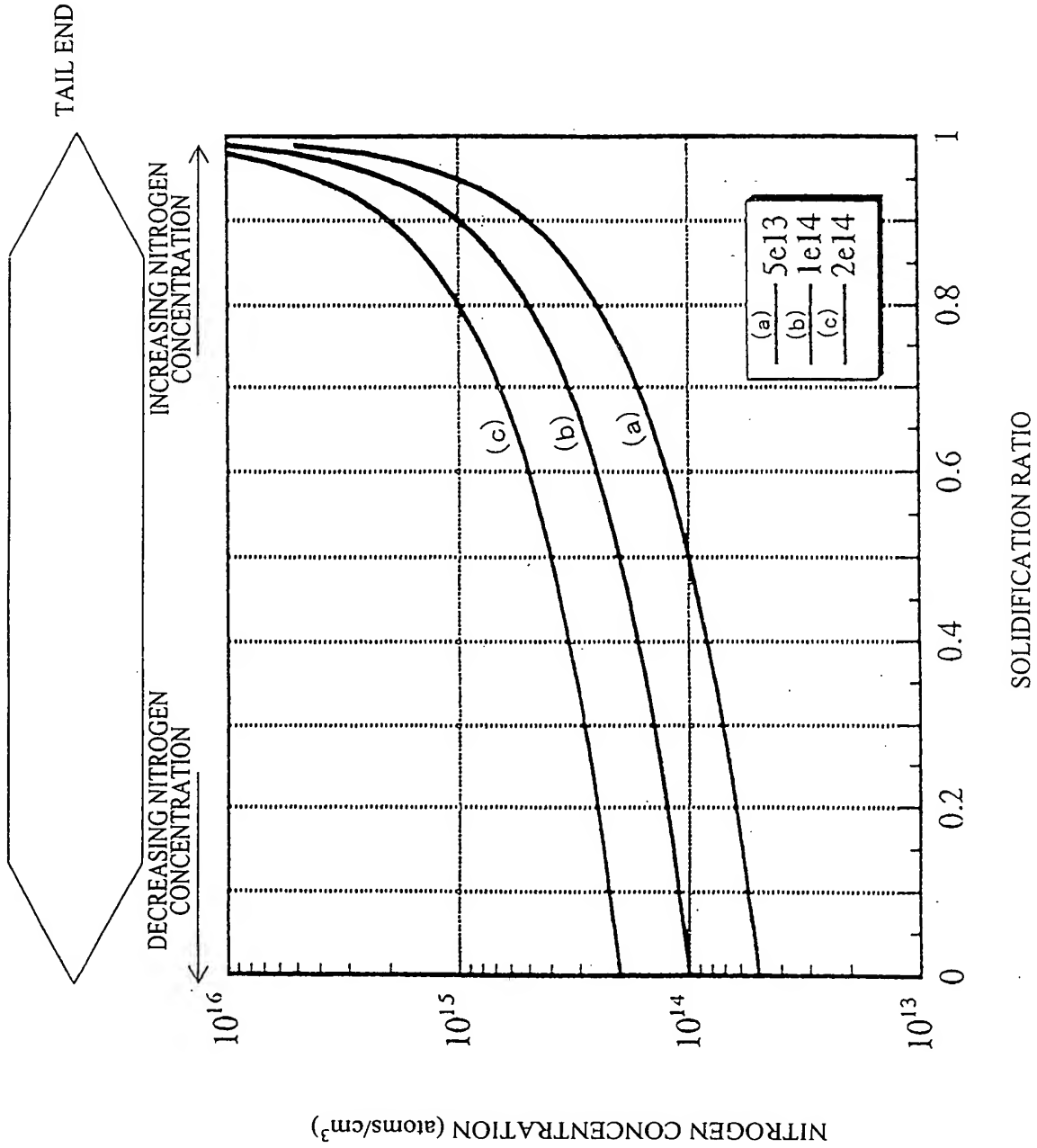


FIG.8